

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

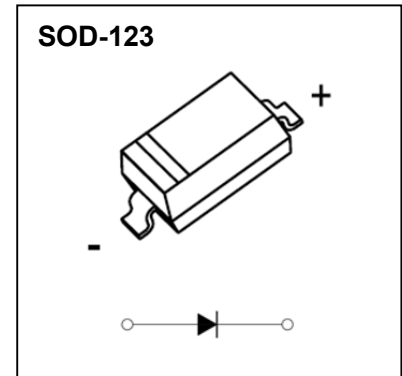
Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

Marking:S8



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	40	V
Reverse Voltage	V _R	30	V
Mean Rectifying Current	I _O	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	200	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I _F = 1 mA	V _F	-	0.37	V
Reverse Current at V _R = 30 V	I _R	-	0.5	μA
Capacitance Between Terminals at V _R = 1 V, f = 1 MHz	C _T	2	-	pF

Note: ESD sensitive product handling required.

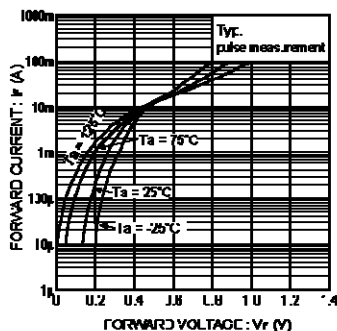


Fig. 1 Forward characteristics

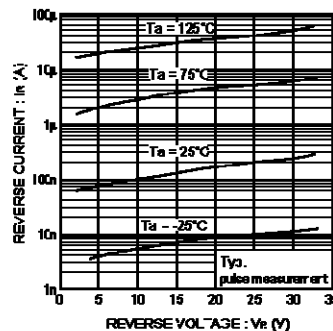


Fig. 2 Reverse characteristics

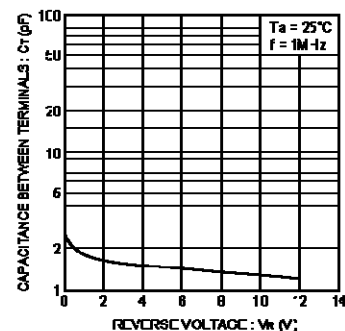


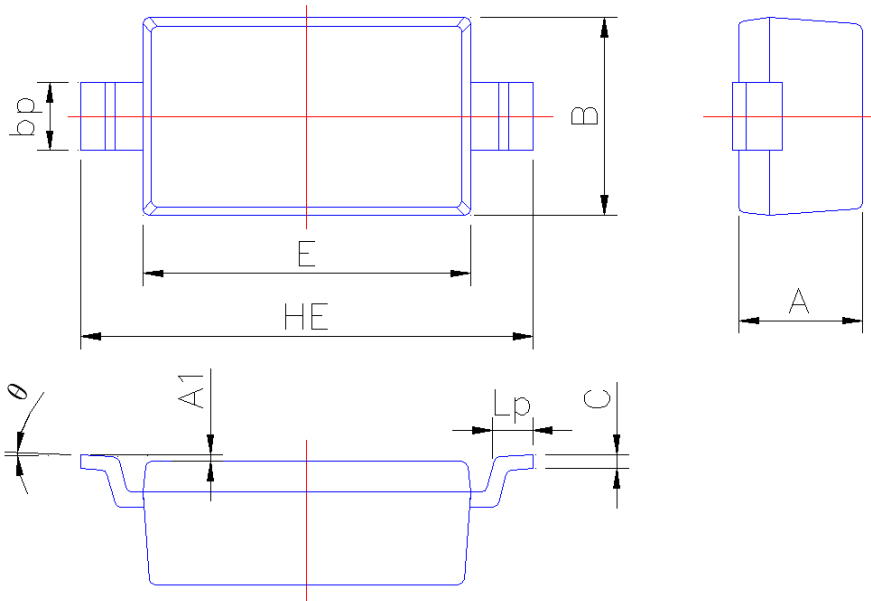
Fig. 3 Capacitance between terminals characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.01	0.100
B	1.55	1.65
bp	0.50	0.70
C	0.09	0.150
E	2.60	2.70
HE	3.45	3.85
Lp	0.20	0.45
θ	0°	5°